

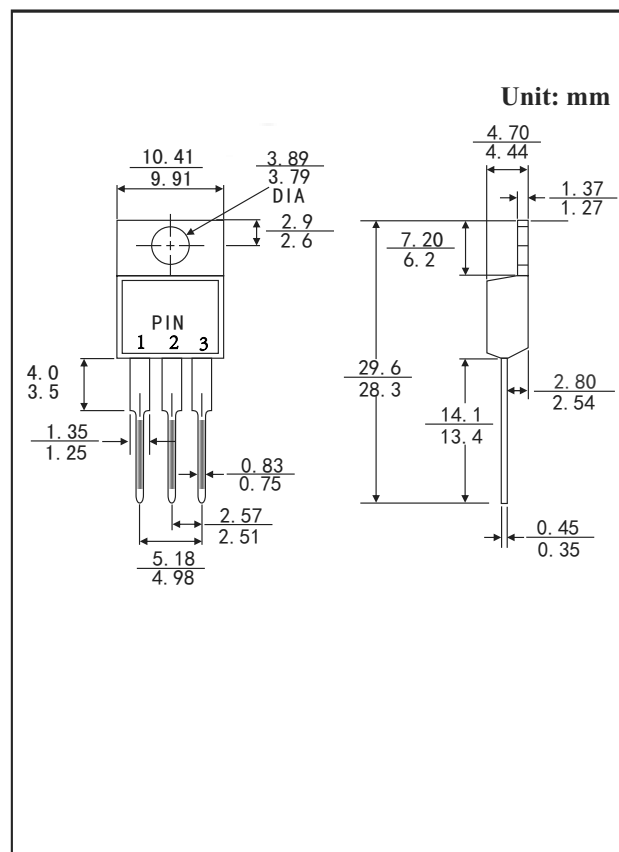
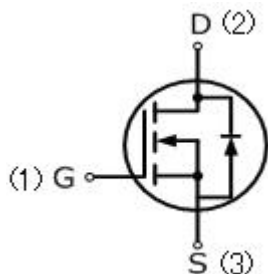
TO-220AB 4A, 650V N-CHANNEL POWER MOSFET
FEATURE

- 4A,650V, $R_{DS(ON)MAX}=2.92\ \Omega$ @ $V_{GS}=10V/2A$
- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

■ SYMBOL

Pin Definition:

1. Gate
2. Drain
3. Source


Absolute Maximum Ratings ($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	4N65	UNIT
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	I_D	4	A
Pulsed Drain Current (Note1)	I_{DM}	16	
Single Pulse Avalanche Energy (Note 2)	E_{AS}	138	mJ
Reverse Diode dv/dt (Note 3)	dv/dt	5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55to+150	$^\circ\text{C}$
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$

Parameter	Symbol	4N65	Units
Thermal resistance , Channel to Case	$R_{th(ch-c)}$	4.17	$^\circ\text{C}/\text{W}$
Maximum Power Dissipation	P_D	30	W

Electrical Characteristics (T _c =25°C,unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	650	—	—	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V,V _{GS} =0V	—	—	1	uA
Gate-Body Leakage Current,Forward	I _{GSSF}	V _{GS} =30V,V _{DS} =0V	—	—	100	nA
Gate-Body Leakage Current,Reverse	I _{GSSR}	V _{GS} =-30V,V _{DS} =0V	—	—	-100	nA
On Characteristics						
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250uA	2.0	—	4.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =2A	—	2.313	2.92	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V, f=1.0MHZ	—	584	—	pF
Output Capacitance	C _{oss}		—	37	—	pF
Reverse Transfer Capacitance	C _{rss}		—	27	—	pF
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	V _{DD} =325V,I _D =4A, R _G =10Ω	—	10.4	—	ns
Turn-On Rise Time	t _r		—	1.2	—	ns
Turn-Off Delay Time	t _{d(off)}		—	21.6	—	ns
Turn-Off Fall Time	t _f		—	4	—	ns
Total Gate Charge	Q _g	V _{DS} =520V,I _D =4A, V _{GS} =10V	—	12.8	—	nC
Gate-Source Charge	Q _{gs}		—	5.6	—	nC
Gate-Drain Charge	Q _{gd}		—	2.6	—	nC
Drain-Source Body Diode Charcteristics and Maximum Ratings						
Continuous Diode Forward Current	I _S		—	—	4	A
Pulsed Diode Forward Current	I _{SM}		—	—	16	A
Diode Forward Voltage	V _{SD}	I _S =2A,V _{GS} =0V	—	—	1.2	V
Reverse Recovery Time	t _{rr}	V _{DS} =30V,I _F =1A,	—	125	—	ns
Reverse Recovery Charge	Q _{rr}	dI _F /dt=100A/us,(Note3)	—	262	—	nC

Notes

1. Repetitive Rating; pulse width limited by maximum junction temperature.
2. $V_{DD}=50V, L=10mH, R_g=25\Omega$, starting $T_J=25^{\circ}\text{C}$.
3. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

RATING AND CHARACTERISTIC CURVES

Figure.1 Typical Output Characteristics

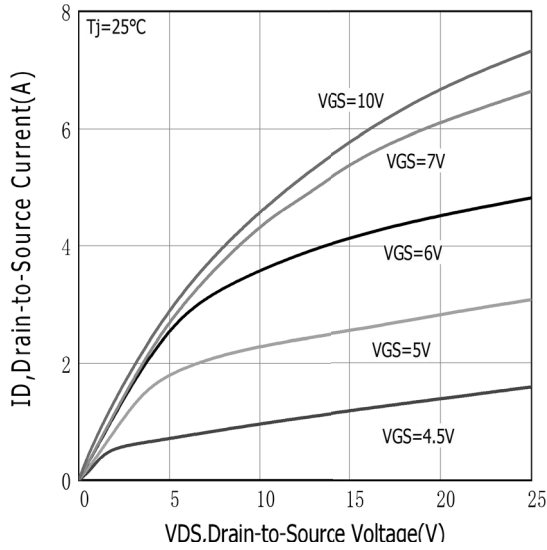


Figure.2 Typical Gate Charge vs Gate to Source Voltage

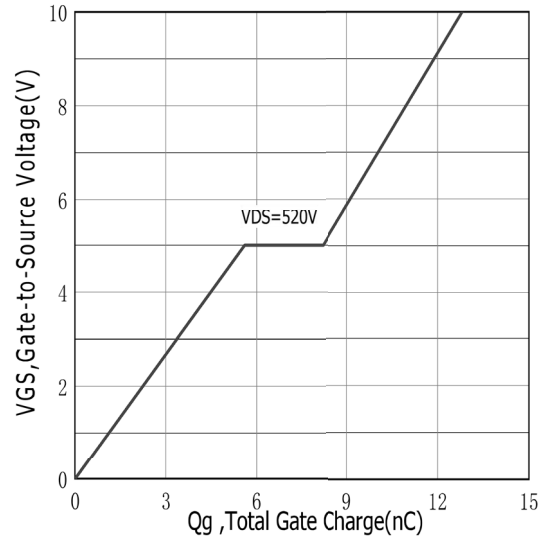


Figure.3 Typical Body Diode Transfer Characteristics

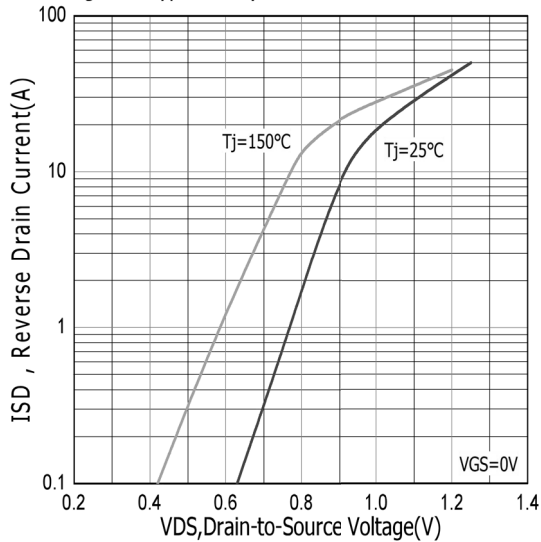


Figure.4 Typical Capacitance vs Drain to Source Voltage

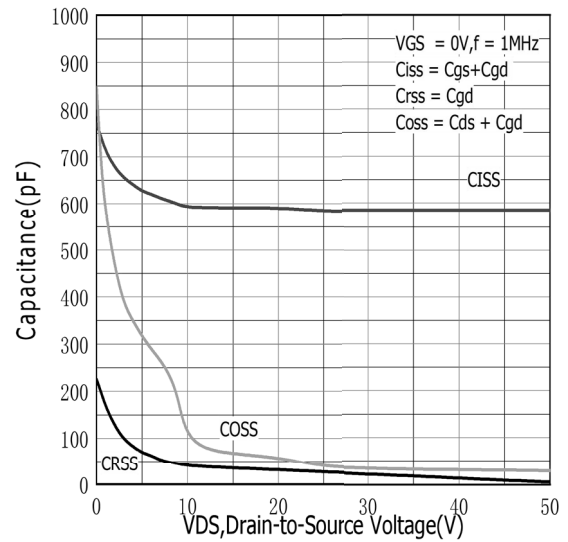


Figure.5 Typical Breakdown Voltage vs Junction Temperature

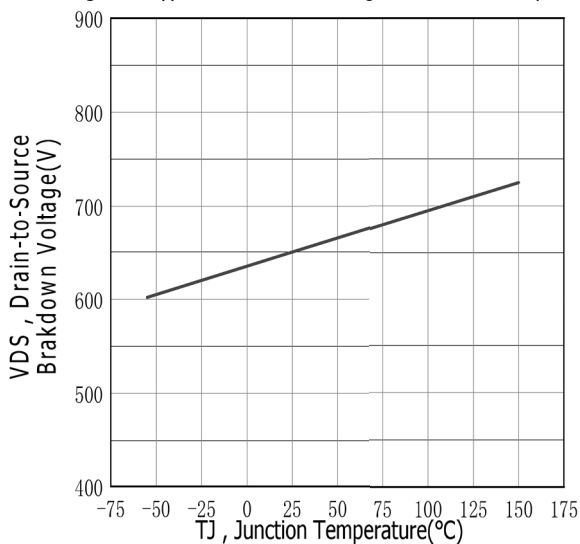


Figure.6 Typical Drain to Source on Resistance vs Junction Temperature

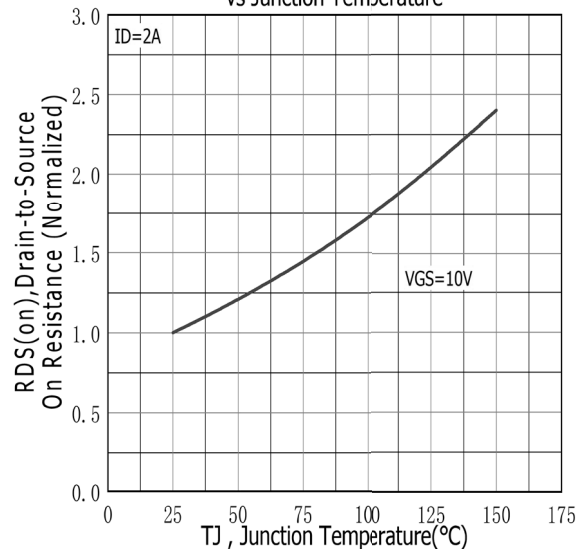


Figure.7 Maximum Forward Bias Safe Operating Area

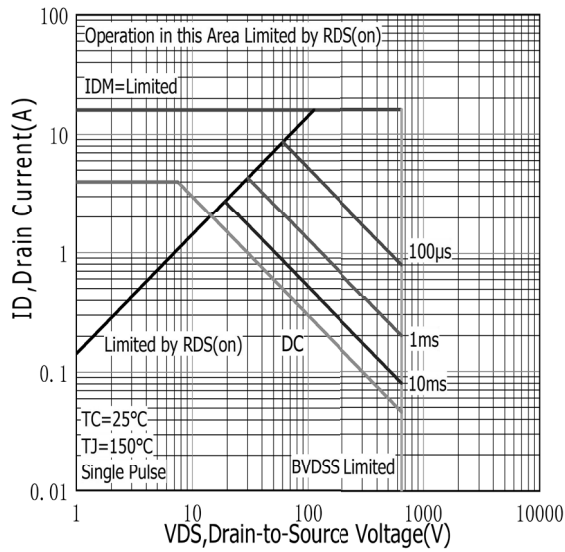


Figure.8 Typical Drain to Source ON Resistance vs Drain Current

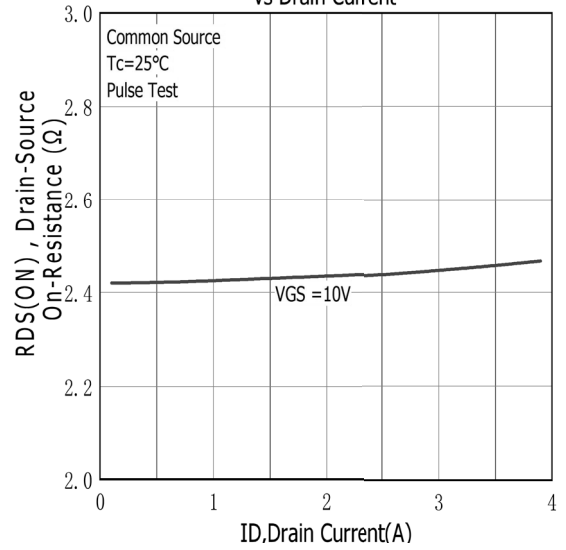


Figure.9 Maximum EAS vs Channel Temperature

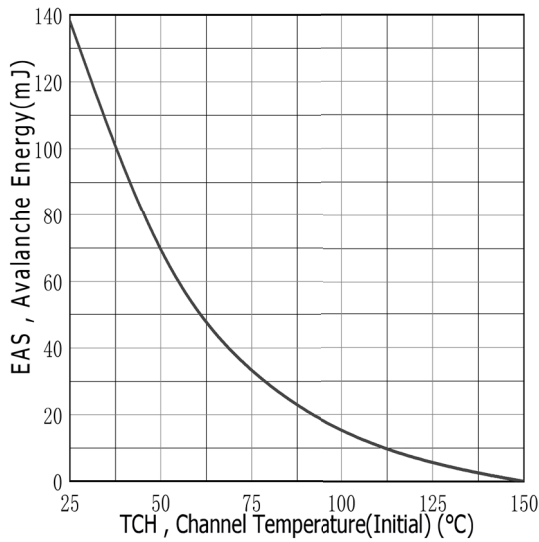


Figure.10 Typical Threshold Voltage vs Case Temperature

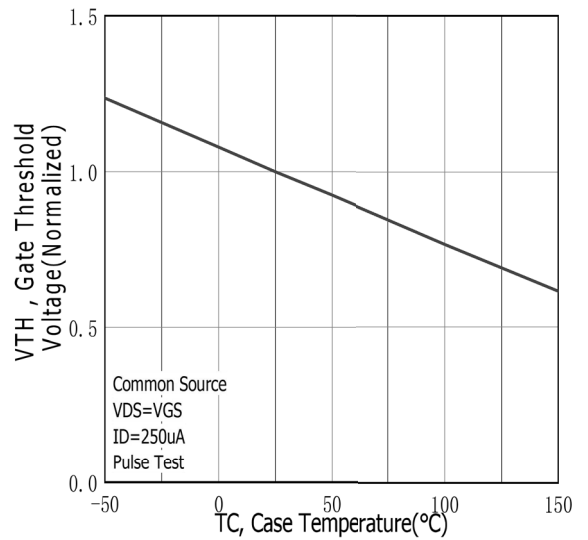


Figure.11 Maximum Effective Thermal Impedance, Junction to Case

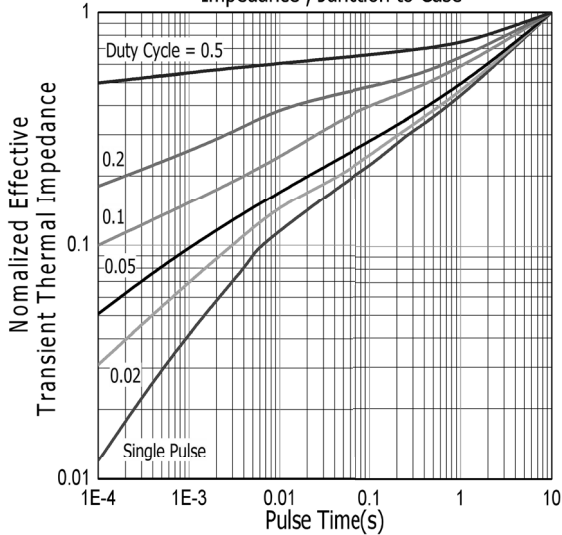


Figure.12 Maximum Power Dissipation vs Case Temperature

